AMENDMENTS TO THE CLAIMS

Please replace the claims, including all prior versions, with the listing of claims below.

Listing of Claims:

1. (Currently amended) ~~Method~~A method for masking first recesses ~~(1)~~ in a structure ~~(4)~~ having webs ~~(4)~~ with a high aspect ratio, comprising a set of recesses ~~(1, 2)~~ having different aspect ratios, ~~in particular a semiconductor structure, having the following steps~~comprising:

- applying a filling layer ~~(5) is applied~~ to the structure ~~(1, 2, 4)~~,

with the filling layer ~~(5) being~~ applied over a fixed distance beyond the webs ~~(4) in~~ such ~~a way~~ that a cavity ~~(6)~~ is formed in the first recesses ~~(1)~~ having a high aspect ratio~~;~~,

- removing the filling layer ~~(5) is removed~~ by means of a planar removal process into ~~the~~an area of the cavity ~~(6)~~ with the filling layer ~~(5) being~~ removed to a defined distance above ~~the~~a surface of the webs ~~(4),~~;

- removing the filling layer ~~(5) is removed~~ in an etching process, with the etching process ~~also~~ attacking in the cavity ~~(6)~~ and, owing to the cavity ~~(6)~~, the filling layer ~~(5) being~~ removed more quickly from the first recess ~~(1)~~ than from recesses ~~(2)~~ without a cavity ~~(6)~~, and ~~with~~ the etching process being stopped after removal of the filling layer ~~(5)~~ from the first recess ~~(1)~~, with the defined distance being ~~chosen~~ selected such that the webs ~~(4)~~ are not underetched in ~~the~~an area of a recess ~~(2)~~ with a low aspect ratio during the etching process.

2. (Currently amended) ~~Method~~ The method according to Claim 1, ~~characterized in that~~wherein an isotropic etching method is used as the etching method.

3. (Currently amended) ~~Method~~ The method according to ~~one of Claims 1 or 2, characterized in that~~claim 1, wherein the structure ~~(1, 2, 4)~~ has the webs ~~(4)~~, and ~~in that~~ a sacrificial layer ~~(12)~~ is applied to the surface of the webs ~~(4),~~ before the application of the filling layer ~~(5)~~.

4. (Currently amended) ~~Method~~ The method according to ~~one of Claims 1 to 3, characterized in that~~claim 1, wherein a chemical/mechanical polishing method is used as ~~the~~ a planar removal process.

5. (Currently amended) ~~Method~~ The method according to Claim 4, ~~characterized in that~~wherein the defined distance is chosen to be greater than twice ~~the~~ a maximum thickness ~~(β)~~ of the filling material ~~(5)~~ between ~~a~~the cavity ~~(6)~~ and the structure ~~(4, 3)~~.

6. (Currently amended) ~~Method~~ The method according to ~~one of Claims 1 to 5, characterized in that~~claim 1, wherein the structure ~~(1, 2, 4)~~ is formed from a silicon wafer ~~(3)~~.

7. (Currently amended) ~~Method~~ The method according to ~~one of Claims 1 to 6, characterized in that~~claim 1, wherein a silicon oxide is deposited as the filling layer ~~(5)~~, using a TEOS process.

8. (Currently amended) ~~Method~~ The method according to ~~one of Claims 1 to 7, characterized in that~~claim 1, wherein silicon oxide is deposited as the sacrificial layer ~~(12)~~.

9. (Currently amended) ~~Method~~ The method according to ~~one of Claims 1 to 8, characterized in that~~claim 1, wherein the filling layer ~~(5)~~ is applied over a recess ~~(2)~~ with a low aspect ratio to above ~~the~~a height of the cavity ~~(6)~~.